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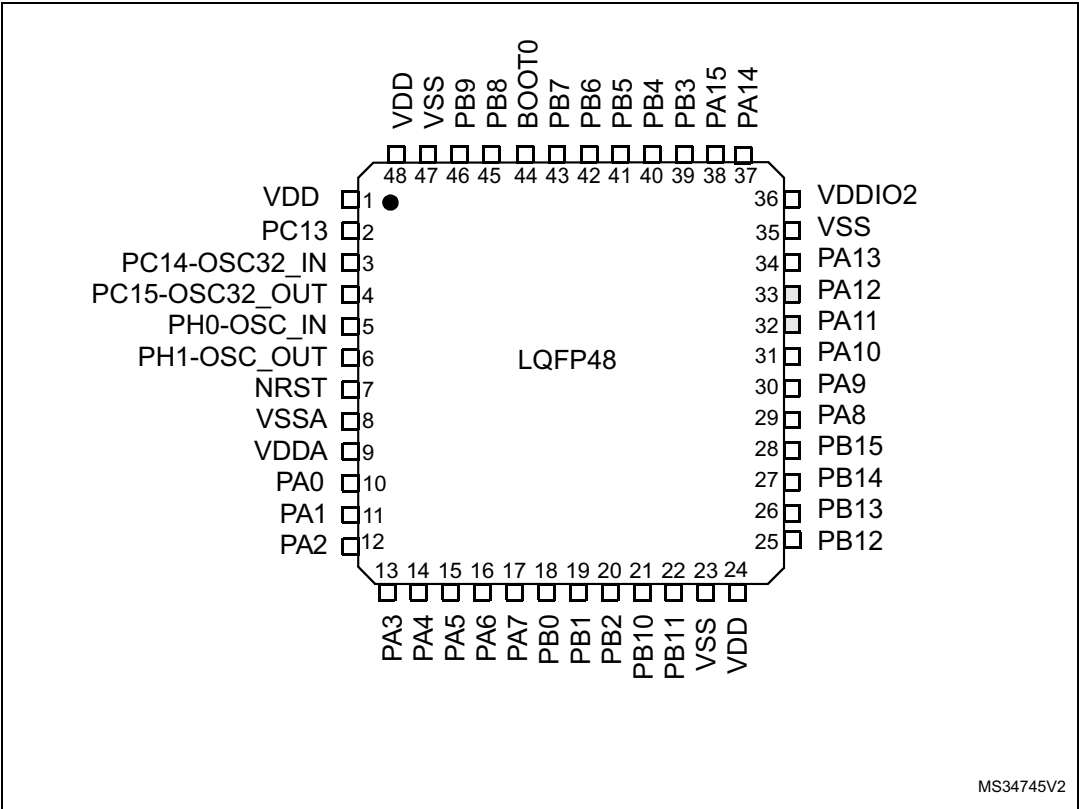
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Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	37
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	6K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 13x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l071czt6

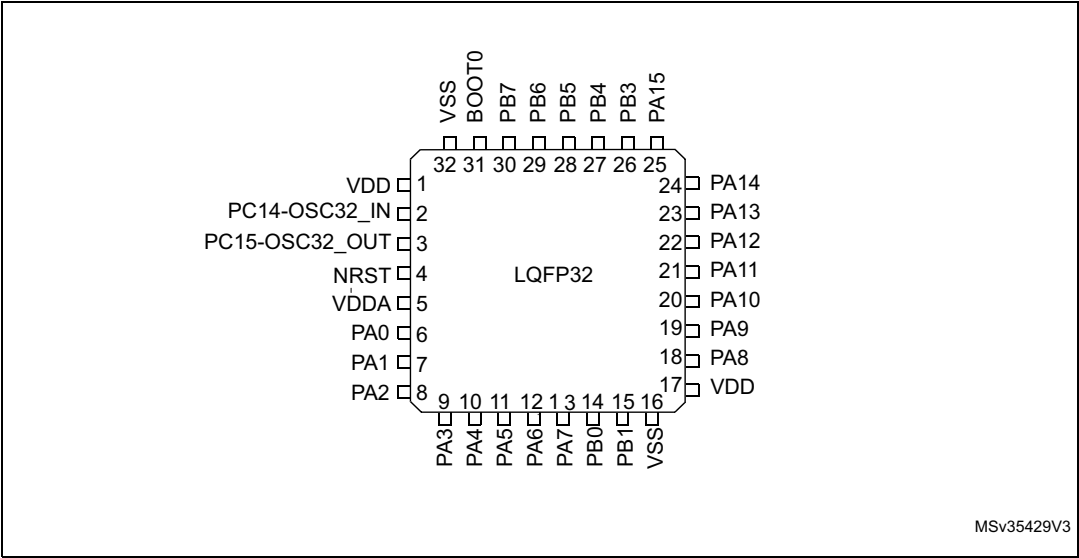
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Figure 8. STM32L071xx LQFP48 pinout - 7 x 7 mm



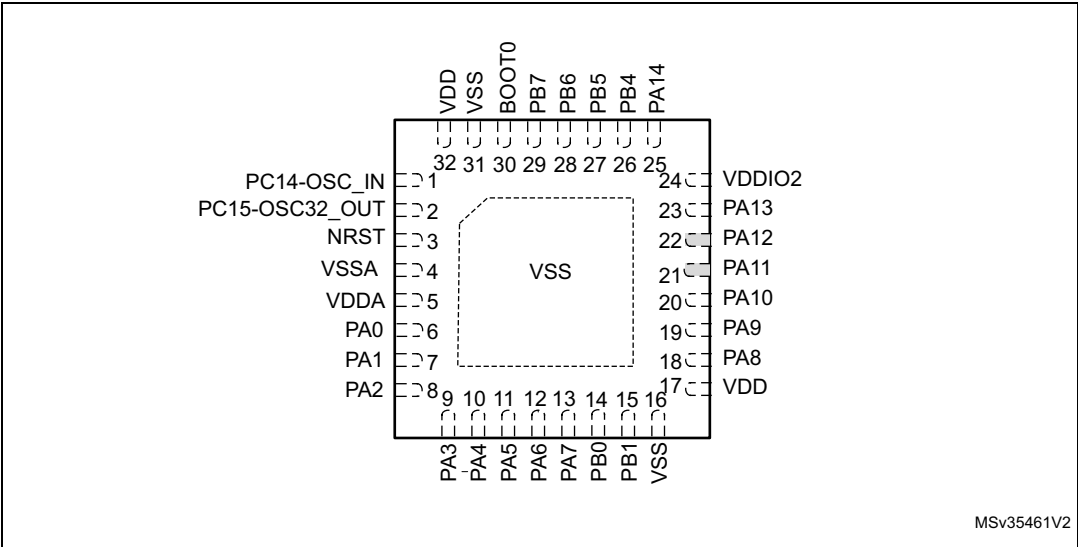
1. The above figure shows the package top view.
2. I/O supplied by VDDIO2.

Figure 9. STM32L071xx LQFP32 pinout



1. The above figure shows the package top view.

Figure 10. STM32L071xx UFQFPN32 pinout



MSv35461V2

1. The above figure shows the package top view.
2. I/O supplied by VDDIO2.

Table 14. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input / output pin
I/O structure	FT	5 V tolerant I/O
	FTf	5 V tolerant I/O, FM+ capable
	TC	Standard 3.3V I/O
	B	Dedicated BOOT0 pin
	RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset.	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers
	Additional functions	Functions directly selected/enabled through peripheral registers

Table 15. STM32L071xxx pin definition (continued)

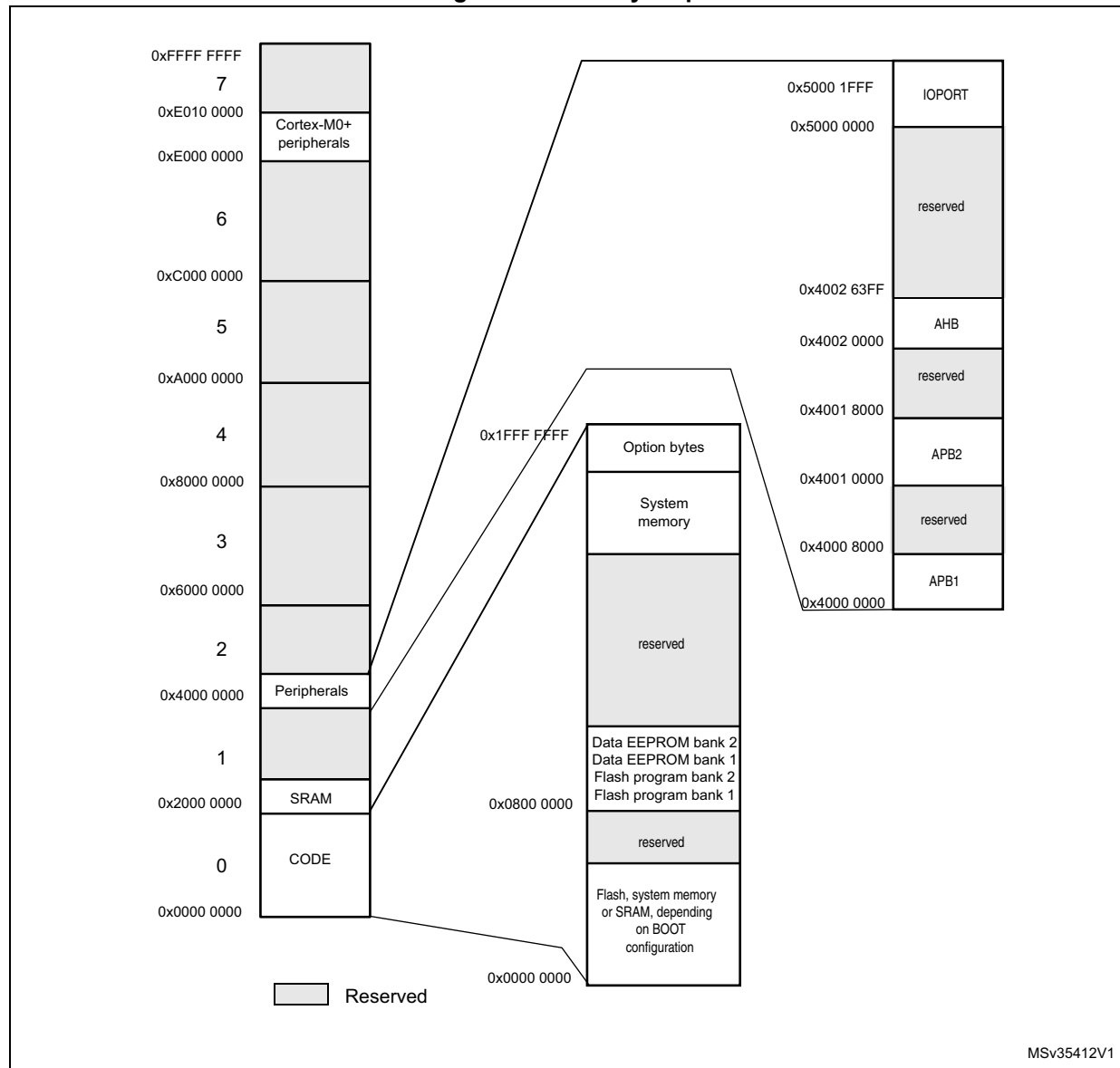
Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32 ⁽¹⁾	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100						
-	-	-	39	E8	-	65	E10	PC8	I/O	FT	-	TIM22_ETR, TIM3_CH3	-
-	-	-	40	D8	-	66	D12	PC9	I/O	FTf	-	TIM21_ETR, TIM3_CH4, I2C3_SDA	-
18	18	29	41	D7	D1	67	D11	PA8	I/O	FTf	-	MCO, EVENTOUT, USART1_CK, I2C3_SCL	-
19	19	30	42	C7	E2	68	D10	PA9	I/O	FTf	-	MCO, USART1_TX, I2C1_SCL, I2C3_SMBA	-
20	20	31	43	C6	C1	69	C12	PA10	I/O	FTf	-	USART1_RX, I2C1_SDA	-
21	21	32	44	C8	D2	70	B12	PA11	I/O	FT	-	SPI1_MISO, EVENTOUT, USART1_CTS, COMP1_OUT	-
22	22	33	45	B8	B1	71	A12	PA12	I/O	FT	-	SPI1_MOSI, EVENTOUT, USART1_RTS_DE, COMP2_OUT	-
23	23	34	46	A8	C2	72	A11	PA13	I/O	FT	-	SWDIO, LPUART1_RX	-
-	-	-	-	-	-	73	C11	VDD	S		-	-	-
-	-	35	47	D5	-	74	F11	VSS	S		-	-	-
-	24	36	48	E5	A1	75	G11	VDDIO2	S		-	-	-
24	25	37	49	A7	B2	76	A10	PA14	I/O	FT	-	SWCLK, USART2_TX, LPUART1_TX	-
25	-	38	50	A6	A2	77	A9	PA15	I/O	FT	-	SPI1_NSS, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1, USART4_RTS_DE	-
-	-	-	51	B7	-	78	B11	PC10	I/O	FT	-	LPUART1_TX, USART4_TX	-
-	-	-	52	B6	-	79	C10	PC11	I/O	FT	-	LPUART1_RX, USART4_RX	-
-	-	-	53	C5	-	80	B10	PC12	I/O	FT	-	USART5_TX, USART4_CK	-

Table 17. Alternate functions port B

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SPI1/SPI2/I2S2/ USART1/2/ LPUART1/ LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2/I 2C1/TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/LPTIM 1/TIM2/3/EVENT OUT/ SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2/I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/ EVENTOUT	I2C3/LPUART1/ COMP1/2/ TIM3
Port B	PB0	EVENTOUT		TIM3_CH3		-	-	-	-
	PB1	-		TIM3_CH4		LPUART1_RTS_DE	-	-	-
	PB2	-	-	LPTIM1_OUT		-	-	-	I2C3_SMBA
	PB3	SPI1_SCK		TIM2_CH2		EVENTOUT	USART1_RTS_DE	USART5_TX	-
	PB4	SPI1_MISO		TIM3_CH1		TIM22_CH1	USART1_CTS	USART5_RX	I2C3_SDA
	PB5	SPI1_MOSI		LPTIM1_IN1	I2C1_SMBA	TIM3_CH2/ TIM22_CH2	USART1_CK	USART5_CK/ USART5_RTS_D E	-
	PB6	USART1_TX	I2C1_SCL	LPTIM1_ETR		-	-	-	-
	PB7	USART1_RX	I2C1_SDA	LPTIM1_IN2		-	-	USART4_CTS	-
	PB8	-		-		I2C1_SCL	-	-	-
	PB9	-		EVENTOUT	-	I2C1_SDA	SPI2_NSS/ I2S2_WS	-	-
	PB10	-		TIM2_CH3		LPUART1_TX	SPI2_SCK	I2C2_SCL	LPUART1_RX
	PB11	EVENTOUT		TIM2_CH4		LPUART1_RX	-	I2C2_SDA	LPUART1_TX
	PB12	SPI2_NSS/I2S2_WS		LPUART1_RTS_ DE			I2C2_SMBA	EVENTOUT	-
	PB13	SPI2_SCK/I2S2_CK		MCO		LPUART1_CTS	I2C2_SCL	TIM21_CH1	-
	PB14	SPI2_MISO/ I2S2_MCK		RTC_OUT		LPUART1_RTS_DE	I2C2_SDA	TIM21_CH2	-
	PB15	SPI2_MOSI/ I2S2_SD		RTC_REFIN	-	-	-	-	-

5 Memory mapping

Figure 11. Memory map



1. Refer to the STM32L071xx reference manual for details on the Flash memory organization for each memory size.

6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the ambient temperature condition summarized in [Table 25](#).

Table 26. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{VDD}^{(1)}$	V_{DD} rise time rate	BOR detector enabled	0	-	∞	$\mu s/V$
		BOR detector disabled	0	-	1000	
	V_{DD} fall time rate	BOR detector enabled	20	-	∞	
		BOR detector disabled	0	-	1000	
$T_{RSTTEMPO}^{(1)}$	Reset temporization	V_{DD} rising, BOR enabled	-	2	3.3	ms
		V_{DD} rising, BOR disabled ⁽²⁾	0.4	0.7	1.6	
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1	1.5	1.65	V
		Rising edge	1.3	1.5	1.65	
V_{BOR0}	Brown-out reset threshold 0	Falling edge	1.67	1.7	1.74	
		Rising edge	1.69	1.76	1.8	
V_{BOR1}	Brown-out reset threshold 1	Falling edge	1.87	1.93	1.97	
		Rising edge	1.96	2.03	2.07	
V_{BOR2}	Brown-out reset threshold 2	Falling edge	2.22	2.30	2.35	
		Rising edge	2.31	2.41	2.44	
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.45	2.55	2.6	
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.68	2.8	2.85	
		Rising edge	2.78	2.9	2.95	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	

Figure 18. I_{DD} vs V_{DD} , at $T_A = 25^\circ\text{C}$, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS

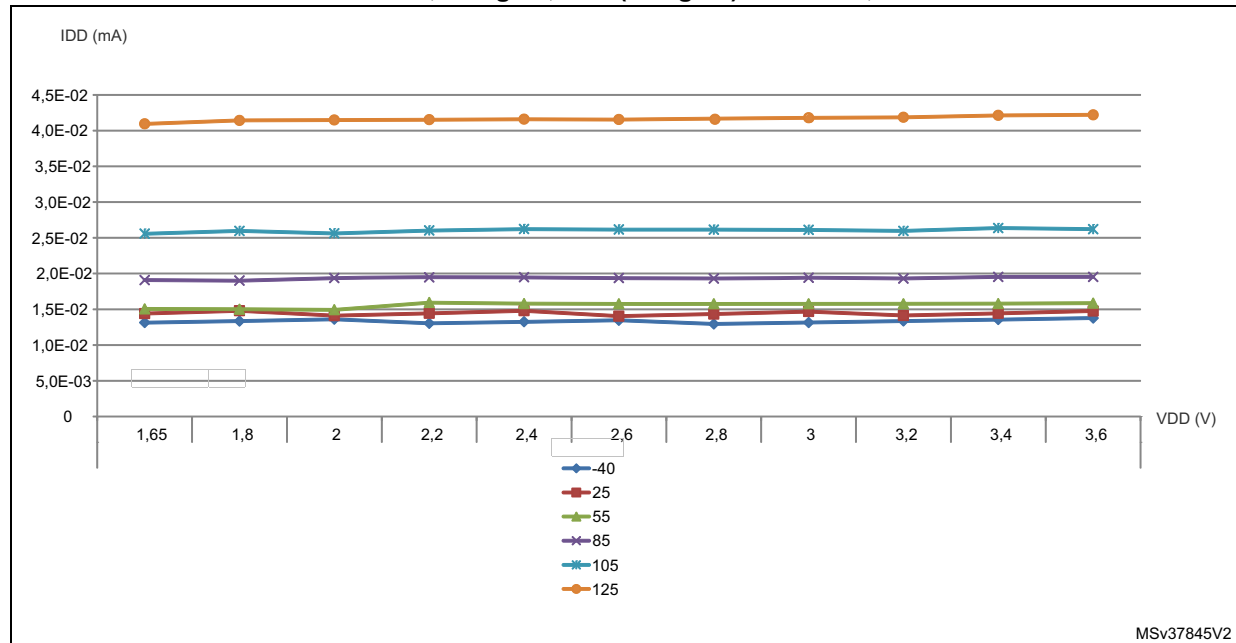


Table 35. Current consumption in Low-power sleep mode

Symbol	Parameter	Condition			Typ	Max (1)	Unit
I_{DD} (LP Sleep)	Supply current in Low-power sleep mode	All peripherals OFF, code executed from Flash memory, V_{DD} from 1.65 to 3.6 V	MSI clock = 65 kHz, $f_{HCLK} = 32$ kHz, Flash memory OFF	$T_A = -40$ to 25°C	4,7	-	μA
			MSI clock = 65 kHz, $f_{HCLK} = 32$ kHz	$T_A = -40$ to 25°C	17	24	
				$T_A = 85^\circ\text{C}$	19,5	30	
				$T_A = 105^\circ\text{C}$	23	47	
				$T_A = 125^\circ\text{C}$	32,5	70	
			MSI clock = 65 kHz, $f_{HCLK} = 65$ kHz	$T_A = -40$ to 25°C	17	24	
				$T_A = 85^\circ\text{C}$	20	31	
				$T_A = 105^\circ\text{C}$	23,5	47	
				$T_A = 125^\circ\text{C}$	32,5	70	
			MSI clock = 131kHz, $f_{HCLK} = 131$ kHz	$T_A = -40$ to 25°C	19,5	27	
				$T_A = 55^\circ\text{C}$	20,5	28	
				$T_A = 85^\circ\text{C}$	22,5	33	
				$T_A = 105^\circ\text{C}$	26	50	
				$T_A = 125^\circ\text{C}$	35	73	

1. Guaranteed by characterization results at 125°C , unless otherwise specified.

Table 38. Average current consumption during Wakeup

Symbol	parameter	System frequency	Current consumption during wakeup	Unit
I_{DD} (Wakeup from Stop)	Supply current during Wakeup from Stop mode	HSI	1	mA
		HSI/4	0,7	
		MSI clock = 4,2 MHz	0,7	
		MSI clock = 1,05 MHz	0,4	
		MSI clock = 65 KHz	0,1	
I_{DD} (Reset)	Reset pin pulled down	-	0,21	
I_{DD} (Power-up)	BOR on	-	0,23	
I_{DD} (Wakeup from StandBy)	With Fast wakeup set	MSI clock = 2,1 MHz	0,5	
	With Fast wakeup disabled	MSI clock = 2,1 MHz	0,12	

Table 39. Peripheral current consumption in Run or Sleep mode⁽¹⁾ (continued)

Peripheral		Typical consumption, $V_{DD} = 3.0\text{ V}$, $T_A = 25\text{ °C}$				Unit
		Range 1, $V_{CORE}=1.8\text{ V}$ $VOS[1:0] = 01$	Range 2, $V_{CORE}=1.5\text{ V}$ $VOS[1:0] = 10$	Range 3, $V_{CORE}=1.2\text{ V}$ $VOS[1:0] = 11$	Low-power sleep and run	
Cortex-M0+ core I/O port	GPIOA	3.5	3	2.5	2.5	$\mu\text{A/MHz}$ (f_{HCLK})
	GPIOB	3.5	2.5	2	2.5	
	GPIOC	8.5	6.5	5.5	7	
	GIOD	1	0.5	0.5	0.5	
	GPIOE	8	6	5	6	
	GPIOH	1.5	1	1	0.5	
AHB	CRC	1.5	1	1	1	$\mu\text{A/MHz}$ (f_{HCLK})
	FLASH	0 ⁽³⁾	0 ⁽³⁾	0 ⁽³⁾	0 ⁽³⁾	
	DMA1	10	8	6.5	8.5	
All enabled		204	162	130	202	$\mu\text{A/MHz}$ (f_{HCLK})
PWR		2.5	2	2	1	$\mu\text{A/MHz}$ (f_{HCLK})

1. Data based on differential I_{DD} measurement between all peripherals off and one peripheral with clock enabled, in the following conditions: $f_{HCLK} = 32\text{ MHz}$ (range 1), $f_{HCLK} = 16\text{ MHz}$ (range 2), $f_{HCLK} = 4\text{ MHz}$ (range 3), $f_{HCLK} = 64\text{ kHz}$ (Low-power run/sleep), $f_{APB1} = f_{HCLK}$, $f_{APB2} = f_{HCLK}$, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling. Not tested in production.

2. HSI oscillator is off for this measure.

3. Current consumption is negligible and close to 0 μA .

Table 41. Low-power mode wakeup timings (continued)

Symbol	Parameter	Conditions	Typ	Max	Unit
t_{WUSTOP}	Wakeup from Stop mode, regulator in Run mode	$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$	5.0	8	μs
		$f_{HCLK} = f_{HSI} = 16 \text{ MHz}$	4.9	7	
		$f_{HCLK} = f_{HSI}/4 = 4 \text{ MHz}$	8.0	11	
	Wakeup from Stop mode, regulator in low-power mode	$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage range 1	5.0	8	
		$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage range 2	5.0	8	
		$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage range 3	5.0	8	
		$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	7.3	13	
		$f_{HCLK} = f_{MSI} = 1.05 \text{ MHz}$	13	23	
		$f_{HCLK} = f_{MSI} = 524 \text{ kHz}$	28	38	
		$f_{HCLK} = f_{MSI} = 262 \text{ kHz}$	51	65	
		$f_{HCLK} = f_{MSI} = 131 \text{ kHz}$	100	120	
		$f_{HCLK} = f_{MSI} = 65 \text{ kHz}$	190	260	
		$f_{HCLK} = f_{HSI} = 16 \text{ MHz}$	4.9	7	
		$f_{HCLK} = f_{HSI}/4 = 4 \text{ MHz}$	8.0	11	
	Wakeup from Stop mode, regulator in low-power mode, code running from RAM	$f_{HCLK} = f_{HSI} = 16 \text{ MHz}$	4.9	7	
		$f_{HCLK} = f_{HSI}/4 = 4 \text{ MHz}$	7.9	10	
		$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$	4.7	8	
$t_{WUSTDBY}$	Wakeup from Standby mode FWU bit = 1	$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	65	130	ms
	Wakeup from Standby mode FWU bit = 0	$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	2.2	3	

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 45](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

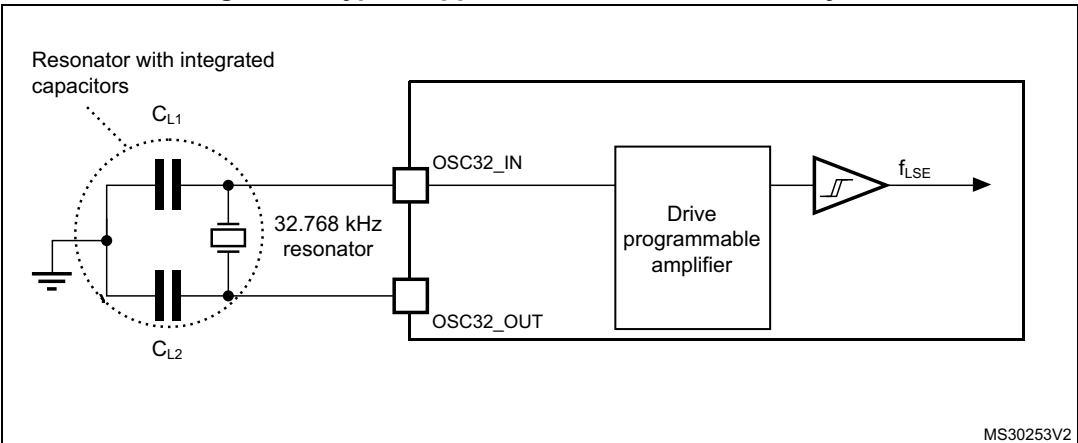
Table 45. LSE oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions ⁽²⁾	Min ⁽²⁾	Typ	Max	Unit
f_{LSE}	LSE oscillator frequency		-	32.768	-	kHz
G_m	Maximum critical crystal transconductance	LSEDRV[1:0]=00 lower driving capability	-	-	0.5	$\mu A/V$
		LSEDRV[1:0]= 01 medium low driving capability	-	-	0.75	
		LSEDRV[1:0] = 10 medium high driving capability	-	-	1.7	
		LSEDRV[1:0]=11 higher driving capability	-	-	2.7	
$t_{SU(LSE)}$ ⁽³⁾	Startup time	V_{DD} is stabilized	-	2	-	s

1. Guaranteed by design.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
3. Guaranteed by characterization results. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer. To increase speed, address a lower-drive quartz with a high- driver mode.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 24. Typical application with a 32.768 kHz crystal



Note: An external resistor is not required between $OSC32_IN$ and $OSC32_OUT$ and it is forbidden to add one.

Table 48. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Typ	Max	Unit
$I_{DD(MSI)}^{(2)}$	MSI oscillator power consumption	MSI range 0	0.75	-	μA
		MSI range 1	1	-	
		MSI range 2	1.5	-	
		MSI range 3	2.5	-	
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	-	
$t_{SU(MSI)}$	MSI oscillator startup time	MSI range 0	30	-	μs
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
		MSI range 4	6	-	
		MSI range 5	5	-	
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	
$t_{STAB(MSI)}^{(2)}$	MSI oscillator stabilization time	MSI range 0	-	40	μs
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
		MSI range 4	-	2.5	
		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
$f_{OVER(MSI)}$	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
		Any range to range 6	-	6	

1. This is a deviation for an individual part, once the initial frequency has been measured.

2. Guaranteed by characterization results.

6.3.13 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in [Table 58](#) are derived from tests performed under the conditions summarized in [Table 25](#). All I/Os are CMOS and TTL compliant.

Table 58. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage	TC, FT, FTf, RST I/Os	-	-	$0.3V_{DD}$	V
		BOOT0 pin	-	-	$0.14V_{DD}^{(1)}$	
V_{IH}	Input high level voltage	All I/Os	$0.7 V_{DD}$	-	-	
V_{hys}	I/O Schmitt trigger voltage hysteresis ⁽²⁾	Standard I/Os	-	$10\% V_{DD}^{(3)}$	-	
		BOOT0 pin	-	0.01	-	
I_{lkg}	Input leakage current ⁽⁴⁾	$V_{SS} \leq V_{IN} \leq V_{DD}$ All I/Os except for PA11, PA12, BOOT0 and FTf I/Os	-	-	± 50	nA
		$V_{SS} \leq V_{IN} \leq V_{DD}$, PA11 and PA12 I/Os	-	-	-50/+250	
		$V_{SS} \leq V_{IN} \leq V_{DD}$ FTf I/Os	-	-	± 100	
		$V_{DD} \leq V_{IN} \leq 5 V$ All I/Os except for PA11, PA12, BOOT0 and FTf I/Os	-	-	200	nA
		$V_{DD} \leq V_{IN} \leq 5 V$ FTf I/Os	-	-	500	
		$V_{DD} \leq V_{IN} \leq 5 V$ PA11, PA12 and BOOT0	-	-	10	μA
R_{PU}	Weak pull-up equivalent resistor ⁽⁵⁾	$V_{IN} = V_{SS}$	30	45	60	k Ω
R_{PD}	Weak pull-down equivalent resistor ⁽⁵⁾	$V_{IN} = V_{DD}$	30	45	60	k Ω
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Guaranteed by characterization.

2. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

3. With a minimum of 200 mV. Guaranteed by characterization results.

4. The max. value may be exceeded if negative current is injected on adjacent pins.

5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

Table 73. SPI characteristics in voltage Range 2 ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	-	8	MHz
		Slave mode Transmitter $1.65 < V_{DD} < 3.6V$			8	
		Slave mode Transmitter $2.7 < V_{DD} < 3.6V$			8 ⁽²⁾	
$Duty_{(SCK)}$	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	$4 \cdot T_{pclk}$	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	$2 \cdot T_{pclk}$	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	$T_{pclk} - 2$	T_{pclk}	$T_{pclk} + 2$	
$t_{su(MI)}$	Data input setup time	Master mode	0	-	-	
$t_{su(SI)}$		Slave mode	3	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	11	-	-	
$t_{h(SI)}$		Slave mode	4.5	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	18	-	52	
$t_{dis(SO)}$	Data output disable time	Slave mode	12	-	42	
$t_{v(SO)}$	Data output valid time	Slave mode	-	20	56.5	
$t_{v(MO)}$		Master mode	-	5	9	
$t_{h(SO)}$	Data output hold time	Slave mode	13	-	-	
$t_{h(MO)}$		Master mode	3	-	-	

1. Guaranteed by characterization results.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while $Duty_{(SCK)} = 50\%$.

I2S characteristics

Table 75. I2S characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main clock output	-	256 x 8K	256x F_s ⁽²⁾	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64x F_s	MHz
		Slave data: 32 bits	-	64x F_s	
D_{CK}	I2S clock frequency duty cycle	Slave receiver	30	70	%
$t_{V(WS)}$	WS valid time	Master mode	-	15	ns
$t_{H(WS)}$	WS hold time	Master mode	11	-	
$t_{su(WS)}$	WS setup time	Slave mode	6	-	
$t_{h(WS)}$	WS hold time	Slave mode	2	-	
$t_{su(SD_MR)}$	Data input setup time	Master receiver	0	-	
$t_{su(SD_SR)}$		Slave receiver	6.5	-	
$t_{h(SD_MR)}$	Data input hold time	Master receiver	18	-	
$t_{h(SD_SR)}$		Slave receiver	15.5	-	
$t_{V(SD_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	77	
$t_{V(SD_MT)}$		Master transmitter (after enable edge)	-	8	
$t_{h(SD_ST)}$	Data output hold time	Slave transmitter (after enable edge)	18	-	
$t_{h(SD_MT)}$		Master transmitter (after enable edge)	1.5	-	

1. Guaranteed by characterization results.

2. 256x F_s maximum value is equal to the maximum clock frequency.

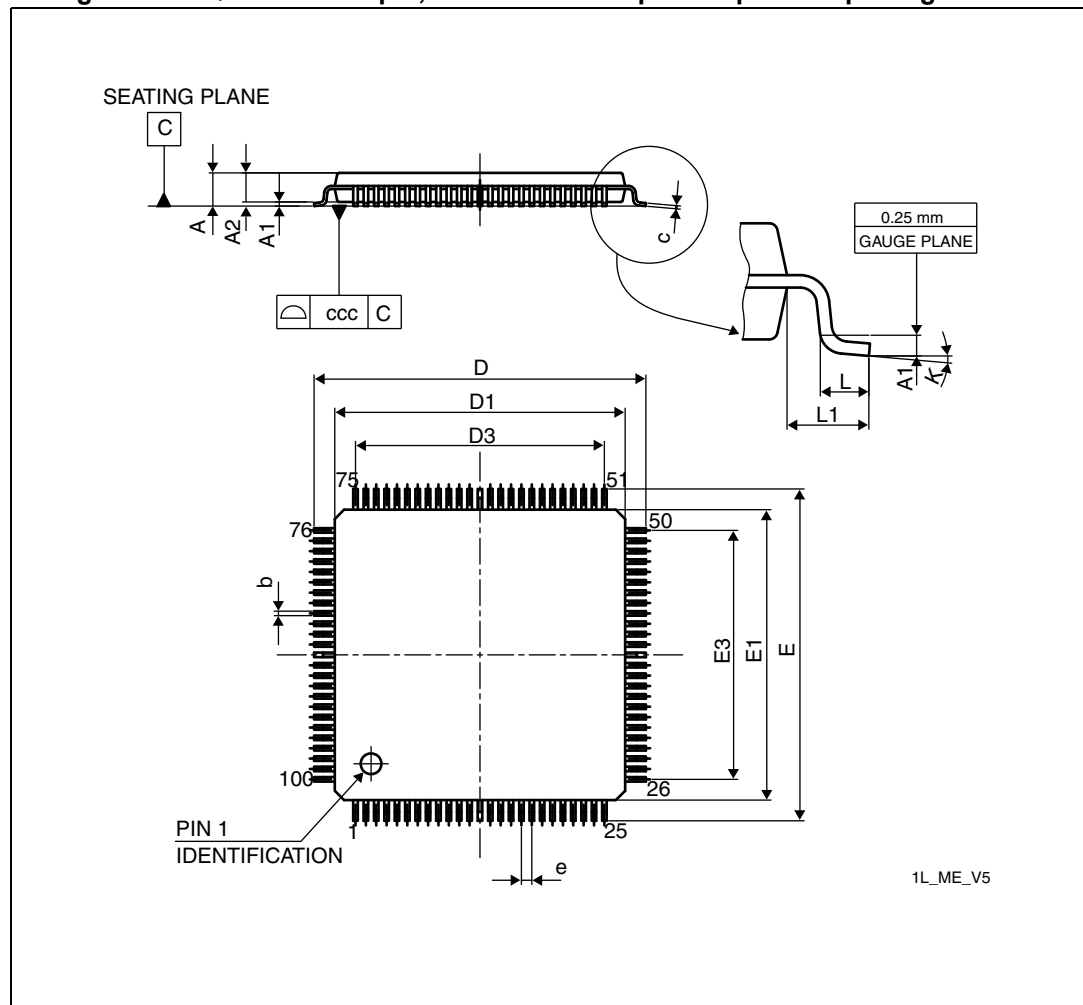
Note: Refer to the I2S section of the product reference manual for more details about the sampling frequency (F_s), f_{MCK} , f_{CK} and D_{CK} values. These values reflect only the digital peripheral behavior, source clock precision might slightly change them. D_{CK} depends mainly on the ODD bit value, digital contribution leads to a min of $(I2SDIV/(2*I2SDIV+ODD))$ and a max of $(I2SDIV+ODD)/(2*I2SDIV+ODD)$. F_s max is supported for each mode/condition.

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status *are available at www.st.com*. ECOPACK® is an ST trademark.

7.1 LQFP100 package information

Figure 39. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline

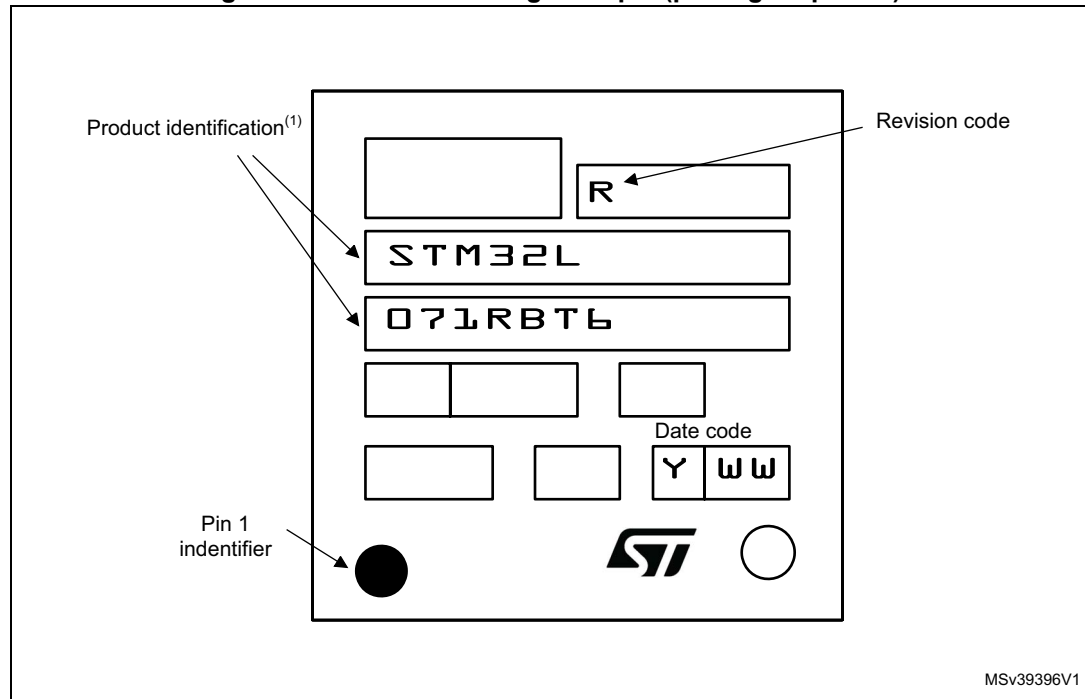


1. Drawing is not to scale. Dimensions are in millimeters.

Device marking for LQFP64

The following figure gives an example of topside marking versus pin 1 position identifier location.

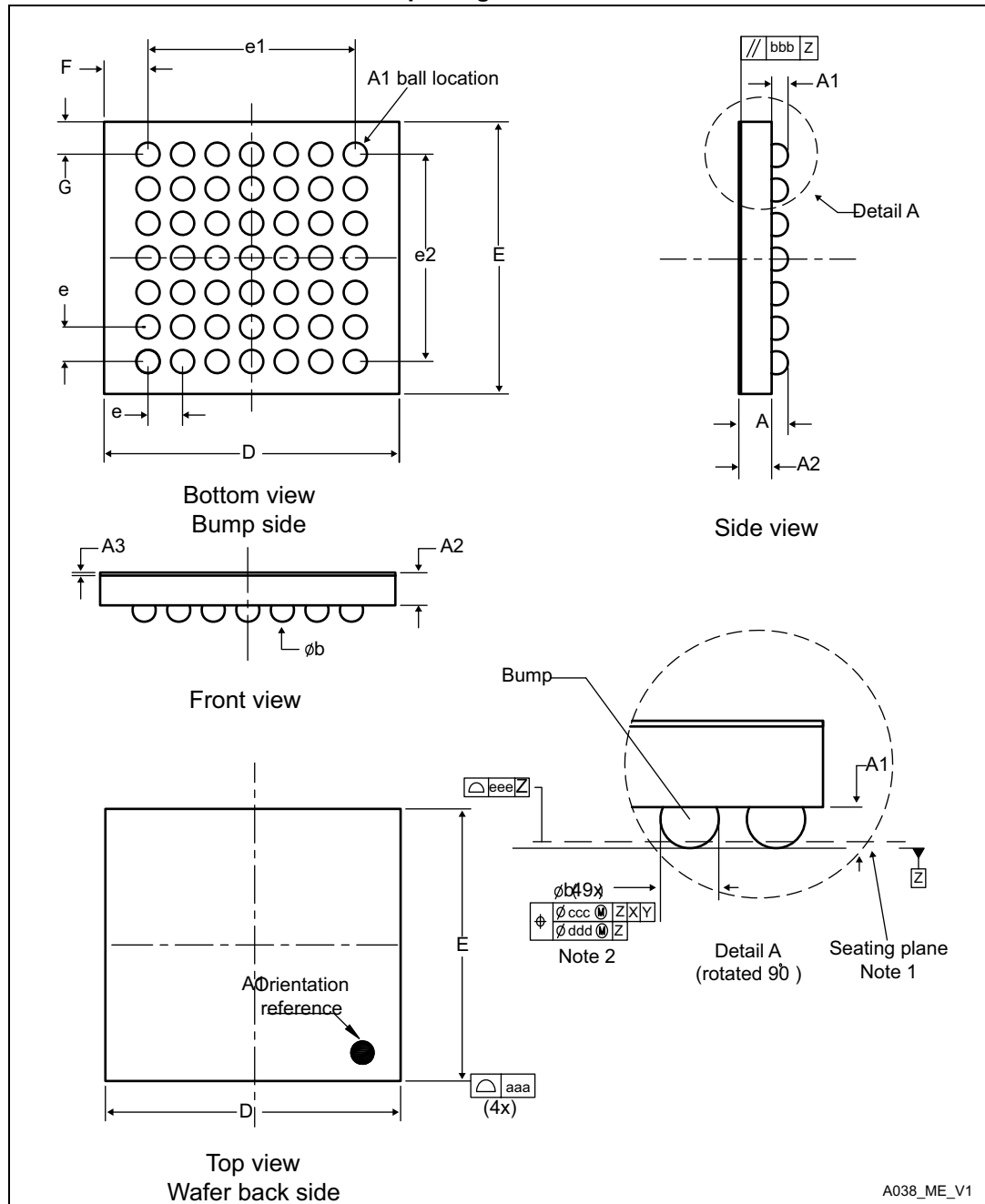
Figure 46. LQFP64 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.5 WLCSP49 package information

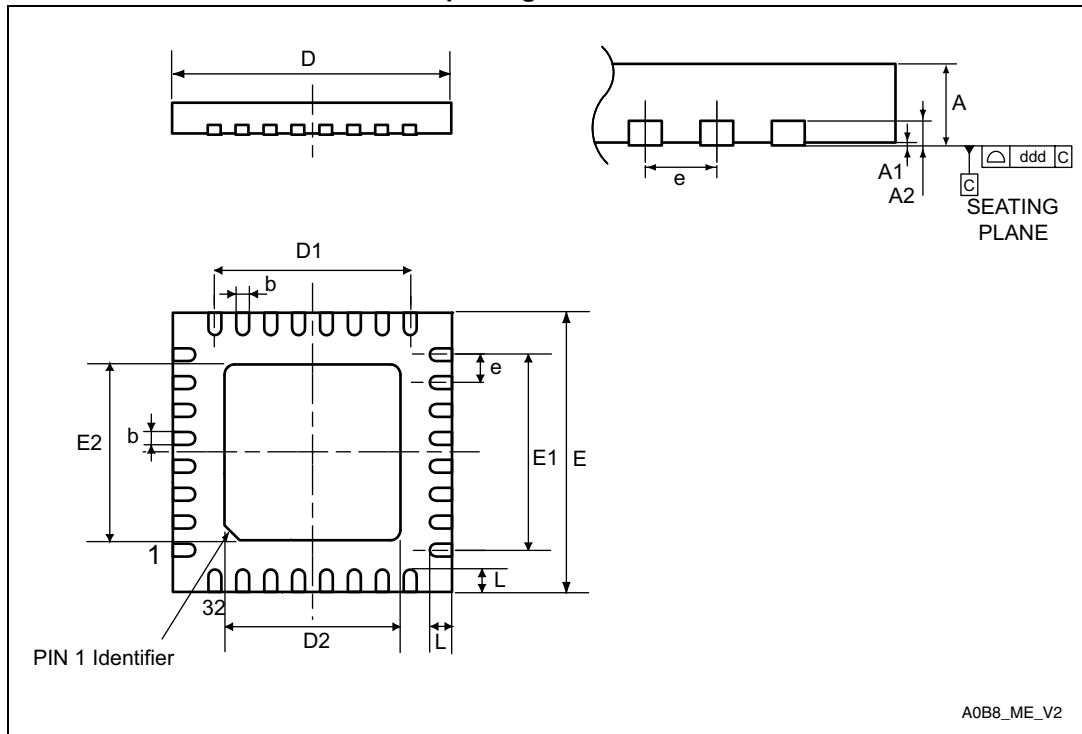
Figure 50. WLCSP49 - 49-pin, 3.294 x 3.258 mm, 0.4 mm pitch wafer level chip scale package outline



1. Drawing is not to scale.

7.8 UFQFPN32 package information

Figure 59. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package outline



1. Drawing is not to scale.